

## 1. Global joint venture starts operations as WeEn Semiconductors

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Thank you for your cooperation and understanding,

WeEn Semiconductors



# **BYC10X-600**

# Rectifier diode, hyperfast

Rev. 03 — 19 October 2017

**Product data sheet** 

# **Product profile**

### 1.1 General description

Hyperfast, epitaxial rectifier diode in a SOD113 (TO-220F) plastic package.

### 1.2 Features

- Extremely fast switching
- Low reverse recovery current
- Reduces switching loss in associated **MOSFET**
- Low thermal resistance
- Isolated package

### 1.3 Applications

- Half-bridge or full-bridge switched-mode Continuous Current Mode (CCM) Power power supplies
- Half-bridge lighting ballasts
- Factor Correction (PFC)

#### 1.4 Quick reference data

- $V_{RRM} \le 600 \text{ V}$
- $V_F = 1.32 \text{ V (typ)}$

- $I_{F(AV)} \le 10 A$
- $t_{rr} = 19 \text{ ns (typ)}$

# **Pinning information**

Table 1. **Pinning** 

Pin	Description	Simplified outline	Graphic symbol
1	cathode (k)		
2	anode (a)	mb	k <del>                                    </del>
mb	mounting base; isolated		
		SOD113 (2-lead TO-220)	F)



# 3. Ordering information

### Table 2. Ordering information

Type number	Package		
	Name	Description	Version
BYC10X-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 'full pack'	SOD113

# 4. Limiting values

#### Table 3. Limiting values

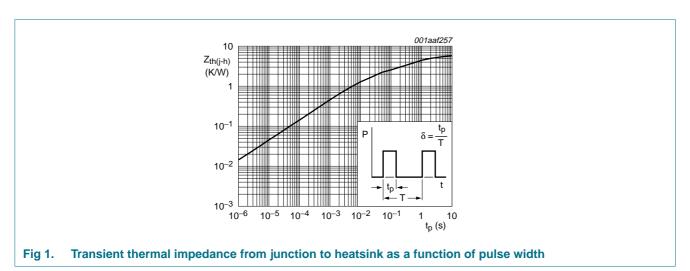
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	600	V
$V_{RWM}$	crest working reverse voltage		-	600	V
$V_R$	reverse voltage	square waveform; $\delta$ = 1.0; $T_h \le 100~^{\circ}C$	-	500	V
I <sub>F(AV)</sub>	average forward current	square waveform; $\delta$ = 0.5; $T_h \le 37$ °C	-	10	Α
I <sub>FRM</sub>	repetitive peak forward current	square waveform; $\delta$ = 0.5; $T_h \le 37$ °C	-	20	Α
I <sub>FSM</sub>	non-repetitive peak forward	t = 10 ms; sinusoidal waveform	-	91	Α
	current	t = 8.3 ms; sinusoidal waveform	-	100	Α
T <sub>stg</sub>	storage temperature		-40	+150	°C
T <sub>i</sub>	junction temperature		-	150	°C

## 5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; see Figure 1	-	-	4.8	K/W
		without heatsink compound	-	-	5.9	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	60	-	K/W



### 6. Isolation characteristics

### Table 5. Isolation limiting values and characteristics

 $T_h = 25 \,^{\circ}C$  unless otherwise specified.

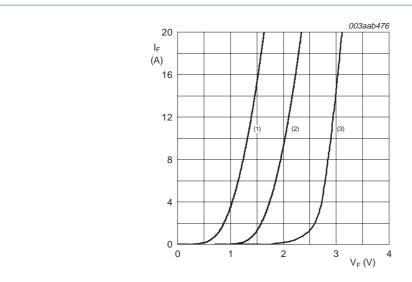
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{\text{isol}(\text{RMS})}$	RMS isolation voltage	from all terminals to external heatsink; $f = 50 \text{ Hz}$ to 60 Hz; sinusoidal waveform; relative humidity $\leq 65 \%$ ; clean and dust free	-	-	2500	V
C <sub>isol</sub>	isolation capacitance	from cathode to external heatsink; f = 1 MHz	-	10	-	pF

## 7. Characteristics

Table 6. Characteristics

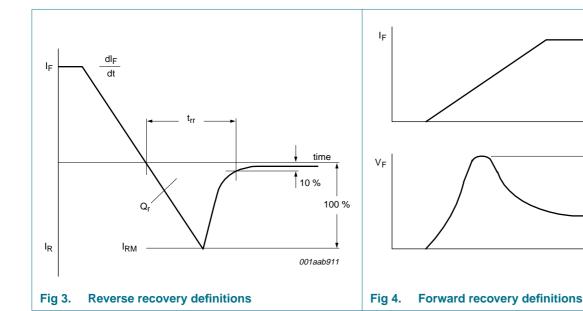
 $T_j = 25 \,^{\circ}C$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	racteristics					
$V_{F}$	forward voltage	$I_F = 10 \text{ A}; T_j = 150 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 2}}{}$	-	1.32	2.03	V
		$I_F = 20 \text{ A}$ ; $T_j = 150 ^{\circ}\text{C}$ ; see Figure 2	-	1.64	2.34	V
		I <sub>F</sub> = 10 A; see <u>Figure 2</u>	-	1.89	2.9	V
$I_R$	reverse current	V <sub>R</sub> = 600 V	-	9	200	μΑ
		$V_R = 500 \text{ V}; T_j = 100 ^{\circ}\text{C}$	-	1.1	3.0	mA
Dynamic c	haracteristics					
t <sub>rr</sub>	reverse recovery time	$I_F$ = 1 A to $V_R$ = 30 V; $dI_F/dt$ = 50 A/ $\mu$ s; see Figure 3	-	35	55	ns
		$I_F = 10 \text{ A to } V_R = 400 \text{ V};$ $dI_F/dt = 500 \text{ A/}\mu\text{s}; \text{ see } \frac{\text{Figure 3}}{}$	-	19	-	ns
		$I_F$ = 10 A to $V_R$ = 400 V; $dI_F/dt$ = 500 A/ $\mu$ s; $T_j$ = 100 °C; see Figure 3	-	32	40	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 10 \text{ A to V}_R = 400 \text{ V};$ $dI_F/dt = 50 \text{ A/}\mu\text{s}; T_j = 125 ^{\circ}\text{C};$ see Figure 3	-	3.0	7.5	A
		$I_F$ = 10 A to $V_R$ = 400 V; $dI_F/dt$ = 500 A/ $\mu$ s; $T_j$ = 100 °C; see Figure 3	-	9.5	12	A
$V_{FR}$	forward recovery voltage	$I_F = 10 \text{ A}$ ; $dI_F/dt = 100 \text{ A}/\mu\text{s}$ ; see Figure 4	-	8	11	V



- (1)  $T_j = 150 \,^{\circ}\text{C}$ ; typical values
- (2)  $T_i = 150 \,^{\circ}\text{C}$ ; maximum values
- (3)  $T_j = 25$  °C; maximum values

Fig 2. Forward current as a function of forward voltage

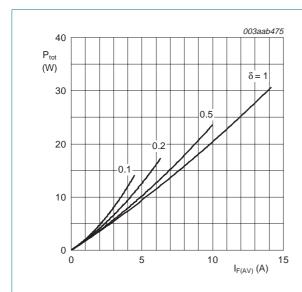


time

 $V_{\mathsf{FR}}$ 

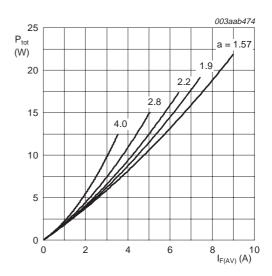
time

001aab912



 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$ 

Fig 5. Forward power dissipation as a function of average forward current; square waveform; maximum values



 $a = form factor = I_{F(RMS)} / I_{F(AV)}$ 

Fig 6. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

## 8. Package outline

Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 'full pack'

SOD113

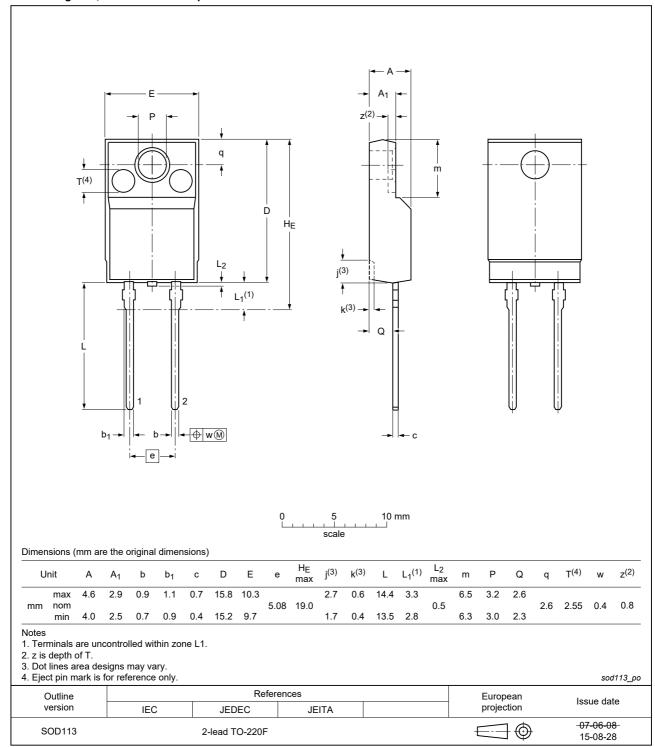


Fig 7. Package outline SOD113 (2-lead TO-220F)



# 9. Revision history

### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYC10X-600_2	20080116	Product data sheet	-	BYC10X-600_1
Modifications:	<ul> <li>Table 3 "Limiting</li> </ul>	ng values", I <sub>F(AV)</sub> and I <sub>FRM</sub> cond	ditions for T $_{ m h}$ changed to 37 $^{\circ}$	C.
BYC10X-600_1	20070831	Product data sheet	-	-

## 10. Legal information

#### 10.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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